

Product Ultra Fast Rectifier Diodes	Type 8GHFSG420-1000									
Metallization Top Au ① Bottom Au ②										
Dimension in mils <table border="1"> <thead> <tr> <th></th> <th>Dimension</th> </tr> </thead> <tbody> <tr> <td>A</td> <td>166±2</td> </tr> <tr> <td>B</td> <td>133(min.)</td> </tr> <tr> <td>D</td> <td>10.5±1.0</td> </tr> <tr> <td>E</td> <td>2(max.)</td> </tr> </tbody> </table>			Dimension	A	166±2	B	133(min.)	D	10.5±1.0	E
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Absolute Maximum Ratings (Ta=25°C)

PEAK REVERSE VOLTAGE VRRM .. 1000 V
FORWARD SURGE CURRENT IFSM.... 300 A
STORAGE TEMPERATURE RANGE Tstg .. -65~150°C

Electrical Characteristics

Item	Symbol	Test Condition	Standard
FORWARD VOLTAGE(for cell type)	VF	IF=20A	1.70 V (MAX)
REVERSE CURRENT	IR	VR=1000V	10µA (MAX)
REVERSE RECOVERY TIME	TRR	RG1	75ns
BREAKDOWN VOLTAGE	BVR	IR=10µA	1050V (MIN)

Quality Yield Assurance per wafer: 70%